

**FEATURES**

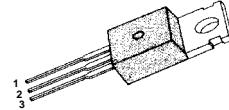
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- 175°C Operating Temperature
- Lower Leakage Current : 10  $\mu$ A (Max.) @  $V_{DS} = 100V$
- Lower  $R_{DS(ON)}$  : 0.289  $\Omega$  (Typ.)

$$BV_{DSS} = 100 V$$

$$R_{DS(on)} = 0.4 \Omega$$

$$I_D = 5.6 A$$

**TO-220**



1.Gate 2. Drain 3. Source

**Absolute Maximum Ratings**

Symbol	Characteristic	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	100	V
$I_D$	Continuous Drain Current ( $T_C=25^\circ C$ )	5.6	A
	Continuous Drain Current ( $T_C=100^\circ C$ )	4	
$I_{DM}$	Drain Current-Pulsed (1)	20	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulsed Avalanche Energy (2)	63	mJ
$I_{AR}$	Avalanche Current (1)	5.6	A
$E_{AR}$	Repetitive Avalanche Energy (1)	3.3	mJ
dv/dt	Peak Diode Recovery dv/dt (2)	6.5	V/ns
$P_D$	Total Power Dissipation ( $T_C=25^\circ C$ )	33	W
	Linear Derating Factor	0.22	
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	- 55 to +175	$^\circ C$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

**Thermal Resistance**

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	4.51	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink	0.5	--	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

### Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$BV_{DSS}$	Drain-Source Breakdown Voltage	100	--	--	V	$V_{GS}=0V, I_D=250\mu\text{A}$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.11	--	V/°C	$I_D=250\mu\text{A}$ <b>See Fig 7</b>
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=5V, I_D=250\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=20V$
	Gate-Source Leakage, Reverse	--	--	-100		$V_{GS}=-20V$
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	10	$\mu\text{A}$	$V_{DS}=100V$
		--	--	100		$V_{DS}=80V, T_C=150^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.4	$\Omega$	$V_{GS}=10V, I_D=2.8A$ (4)
$g_{fs}$	Forward Transconductance	--	3.49	--	S	$V_{DS}=40V, I_D=2.8A$ (4)
$C_{iss}$	Input Capacitance	--	190	240	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ <b>See Fig 5</b>
$C_{oss}$	Output Capacitance	--	55	65		
$C_{rss}$	Reverse Transfer Capacitance	--	21	25		
$t_{d(on)}$	Turn-On Delay Time	--	10	30	ns	$V_{DD}=50V, I_D=5.6A,$ $R_G=24\Omega$ <b>See Fig 13</b> (4)(5)
$t_r$	Rise Time	--	14	40		
$t_{d(off)}$	Turn-Off Delay Time	--	28	70		
$t_f$	Fall Time	--	18	50		
$Q_g$	Total Gate Charge	--	8.5	12	nC	$V_{DS}=80V, V_{GS}=10V,$ $I_D=5.6A$ <b>See Fig 6 &amp; Fig 12</b> (4)(5)
$Q_{gs}$	Gate-Source Charge	--	1.6	--		
$Q_{gd}$	Gate-Drain ("Miller") Charge	--	4.1	--		

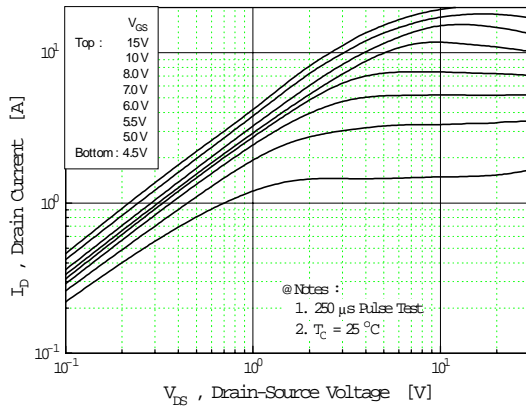
### Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$I_S$	Continuous Source Current	--	--	5.6	A	Integral reverse pn-diode in the MOSFET
$I_{SM}$	Pulsed-Source Current (1)	--	--	20		
$V_{SD}$	Diode Forward Voltage (4)	--	--	1.5	V	$T_J=25^\circ\text{C}, I_S=5.6A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	--	85	--	ns	$T_J=25^\circ\text{C}, I_F=5.6A$
$Q_{rr}$	Reverse Recovery Charge	--	0.23	--	$\mu\text{C}$	$di_F/dt=100A/\mu\text{s}$ (4)

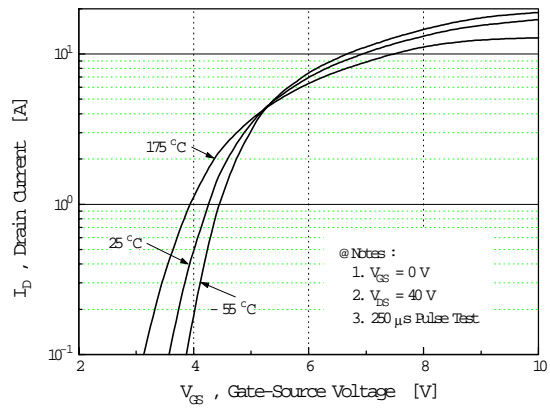
#### Notes ;

- (1) Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- (2)  $L=3\text{mH}, I_{AS}=5.6A, V_{DD}=25V, R_G=27\Omega,$  Starting  $T_J=25^\circ\text{C}$
- (3)  $I_{SD} \leq 5.6A, di/dt \leq 250A/\mu\text{s}, V_{DD} \leq BV_{DSS},$  Starting  $T_J=25^\circ\text{C}$
- (4) Pulse Test : Pulse Width =  $250\mu\text{s},$  Duty Cycle  $\leq 2\%$
- (5) Essentially Independent of Operating Temperature

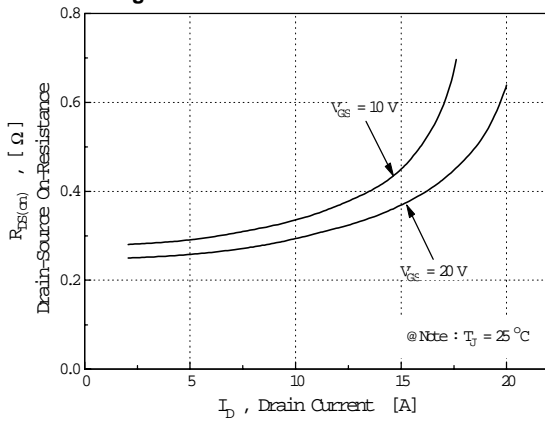
**Fig 1. Output Characteristics**



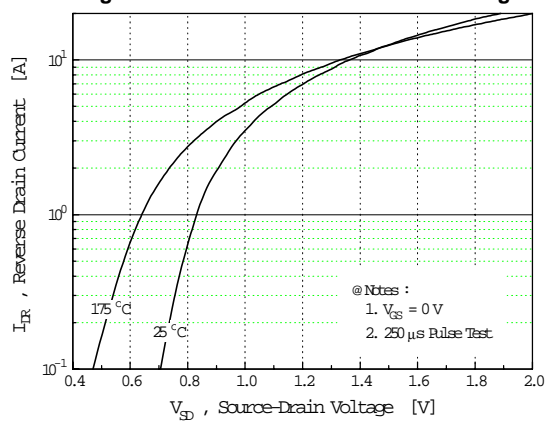
**Fig 2. Transfer Characteristics**



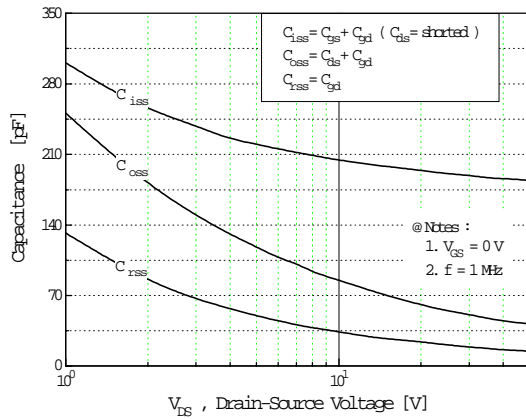
**Fig 3. On-Resistance vs. Drain Current**



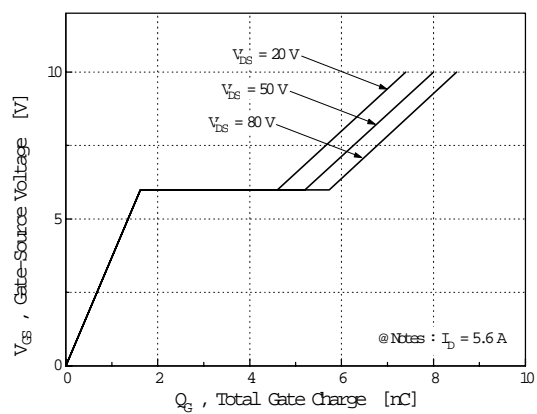
**Fig 4. Source-Drain Diode Forward Voltage**

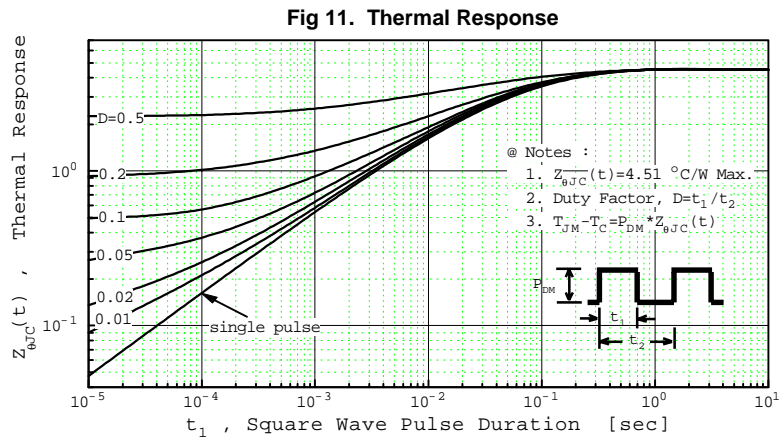
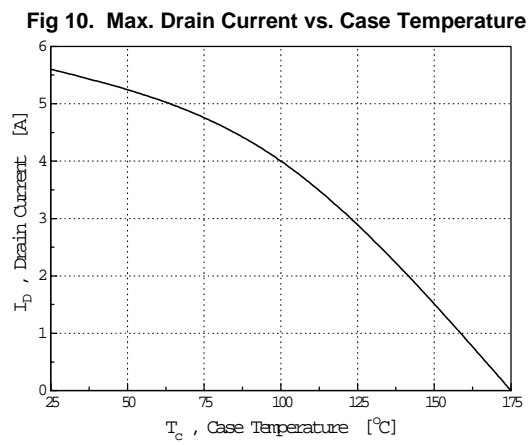
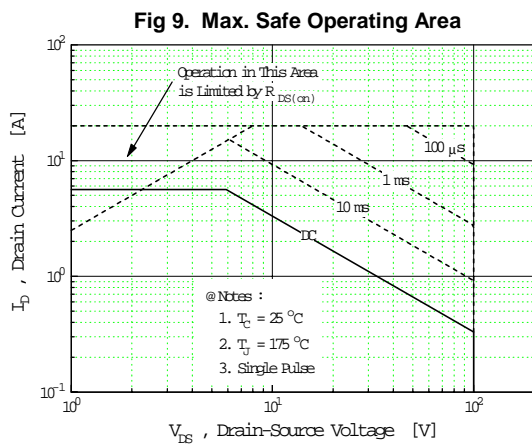
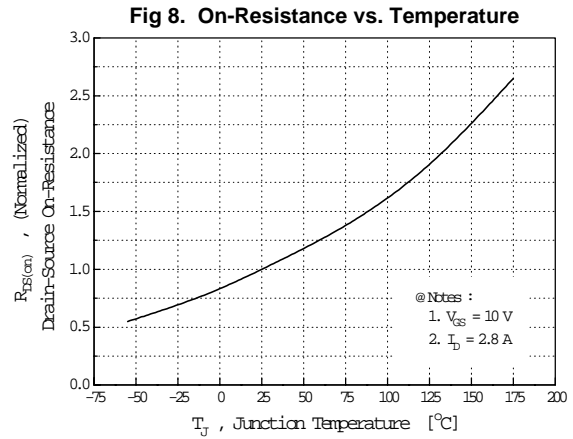
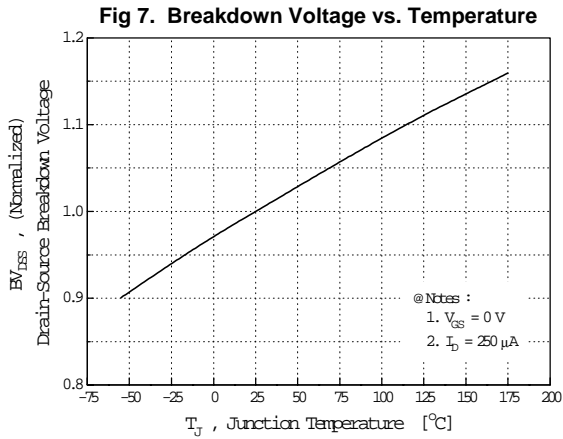


**Fig 5. Capacitance vs. Drain-Source Voltage**

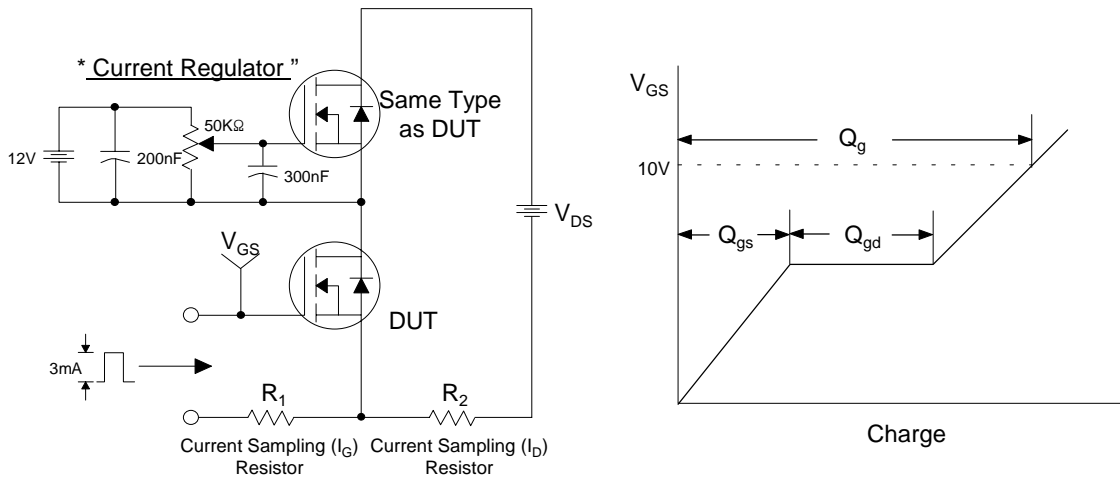


**Fig 6. Gate Charge vs. Gate-Source Voltage**

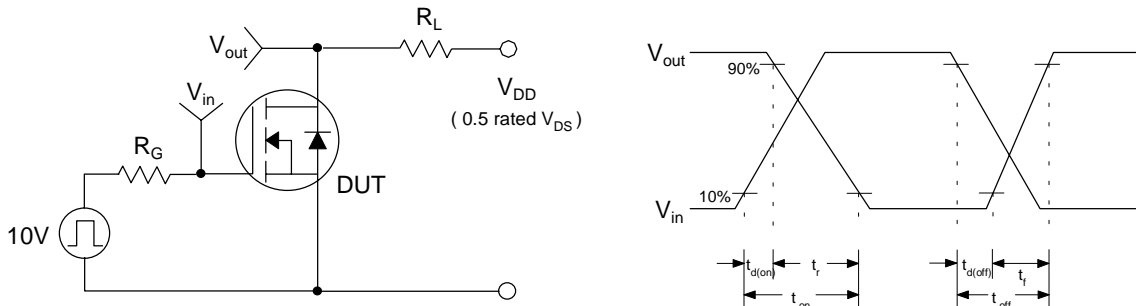




**Fig 12. Gate Charge Test Circuit & Waveform**



**Fig 13. Resistive Switching Test Circuit & Waveforms**



**Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms**

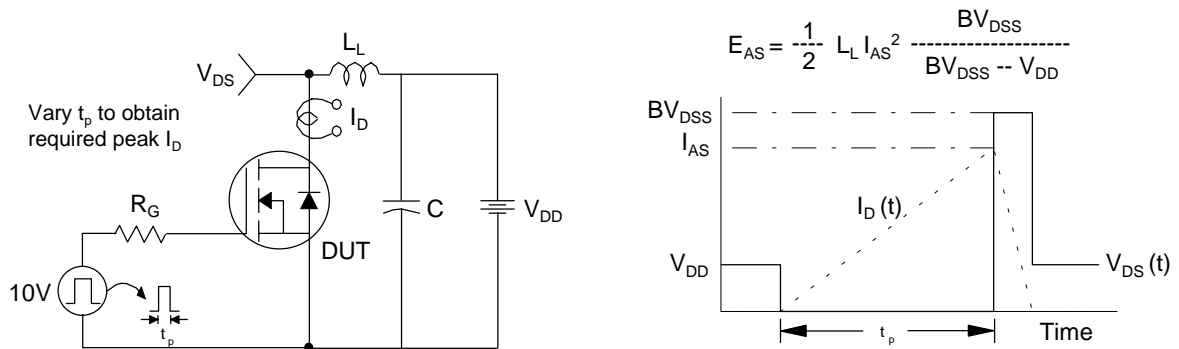
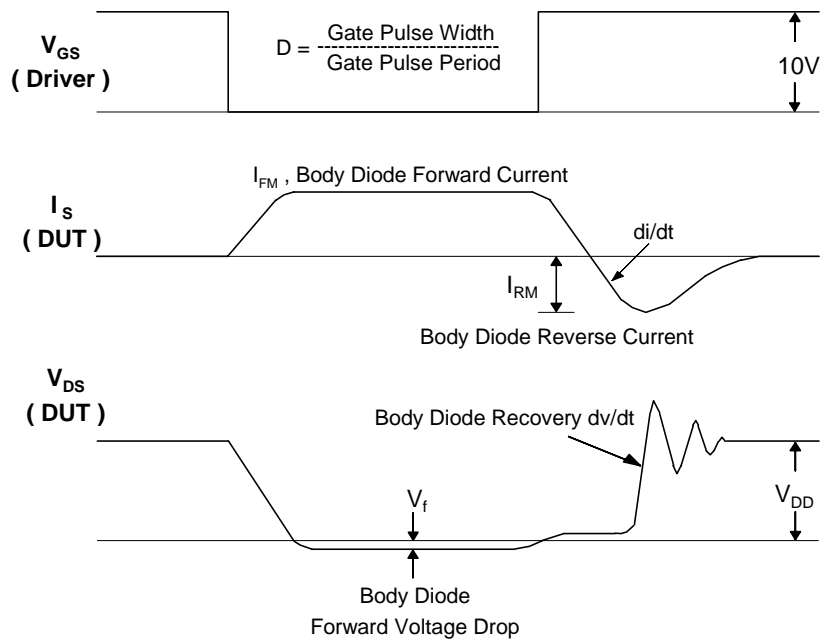
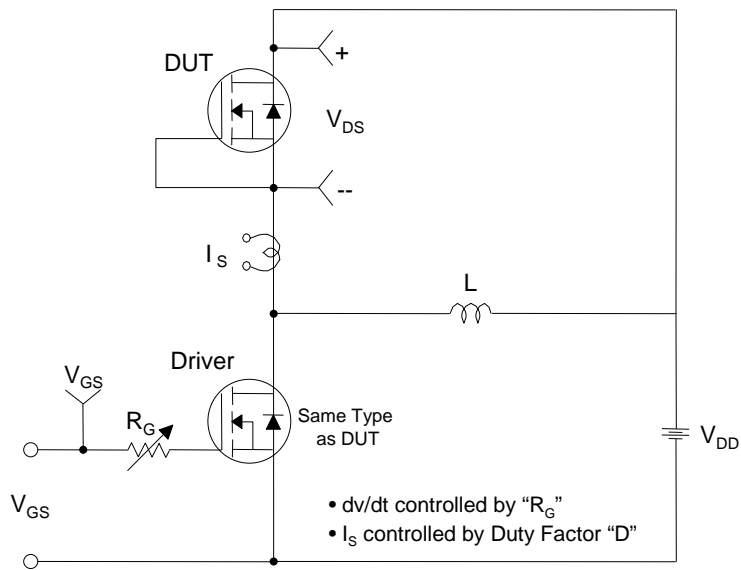


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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